

Docket No.: 4425-317



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Chun-Pei WU

U.S. Patent Application No. 10/643,964

Filed: August 20, 2003

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:
:
: Group Art Unit: 2823
:
: Examiner: HSIEN MING LEE

For: METHOD FOR FABRICATING A MASK READ-ONLY-MEMORY WITH DIODE CELLS

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

- ☒ No additional fee is required.
☐ Small entity status of this application has been established.
☐ Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	20	20	0	x \$ 18 =	\$ 0.00
Independent Claims	2	3	0	x \$ 86 =	\$ 0.00
If multiple claims newly presented, add \$290.00					
Fee for extension of time					
TOTAL FEE DUE					\$ 0.00

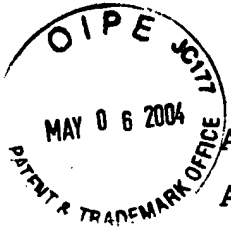
- ☐ A credit card authorization form in the amount of _____ is attached
- ☒ The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 07-1337, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No. : 10/643,964
Applicant : Chun-Pei Wu
Filed : August 20, 2003
TC/A.U. : 2823
Title : METHOD FOR FABRICATING A MASK READ-
ONLY-MEMORY WITH DIODE CELLS
Examiner : LEE, HSIEN MING
Docket No. : 4425-317

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Sir:

In response to the Official Action mailed on February 24, 2004,
please amend the application as follows :

Amendments to the Claims are reflected in the listing of claims which
begin on page 2 of this paper.

Remarks/arguments begin on page 8 of this paper.